

# MCH6663

## Power MOSFET

30V, 188mΩ, 1.8A, -30V, 325mΩ, -1.5A,  
Complementary Dual



ON Semiconductor®

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### Features

- ON-Resistance Nch :  $R_{DS(on)1}=145m\Omega$  (typ)  
Pch :  $R_{DS(on)1}=250m\Omega$  (typ)
- 4V Drive
- Complementary N-Channel and P-Channel MOSFET
- Pb-Free, Halogen Free and RoHS Compliance

### Specifications

Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$

| Parameter                                                                                   | Symbol    | N-channel   | P-channel | Unit |
|---------------------------------------------------------------------------------------------|-----------|-------------|-----------|------|
| Drain to Source Voltage                                                                     | $V_{DSS}$ | 30          | -30       | V    |
| Gate to Source Voltage                                                                      | $V_{GSS}$ | $\pm 20$    | $\pm 20$  | V    |
| Drain Current (DC)                                                                          | $I_D$     | 1.8         | -1.5      | A    |
| Drain Current (Pulse)<br>$PW \leq 10\mu s$ , duty cycle $\leq 1\%$                          | $I_{DP}$  | 7.2         | -6        | A    |
| Power Dissipation<br>When mounted on ceramic substrate<br>(900mm <sup>2</sup> ×0.8mm) 1unit | $P_D$     | 0.8         |           | W    |
| Junction Temperature                                                                        | $T_J$     | 150         |           | °C   |
| Storage Temperature                                                                         | $T_{stg}$ | -55 to +150 |           | °C   |

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

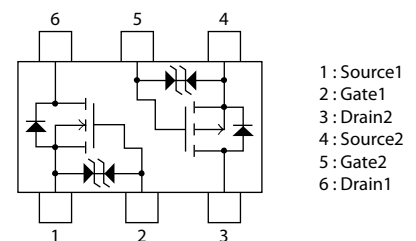
\* Machine Model

### Thermal Resistance Ratings

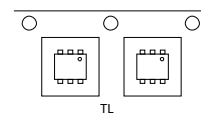
| Parameter                                                                                     | Symbol          | Value  | Unit |
|-----------------------------------------------------------------------------------------------|-----------------|--------|------|
| Junction to Ambient<br>When mounted on ceramic substrate<br>(900mm <sup>2</sup> ×0.8mm) 1unit | $R_{\theta JA}$ | 156.25 | °C/W |

| $V_{DSS}$    | $R_{DS(on)}$ Max | $I_D$ Max |
|--------------|------------------|-----------|
| N-Ch<br>30V  | 188 mΩ@ 10V      | 1.8A      |
|              | 343 mΩ@ 4.5V     |           |
|              | 378 mΩ@ 4V       |           |
| P-Ch<br>-30V | 325 mΩ@ -10V     | -1.5A     |
|              | 555 mΩ@ -4.5V    |           |
|              | 641 mΩ@ -4V      |           |

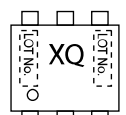
### Electrical Connection N-Channel and P-Channel



### Packing Type : TL



### Marking



Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

# MCH6663

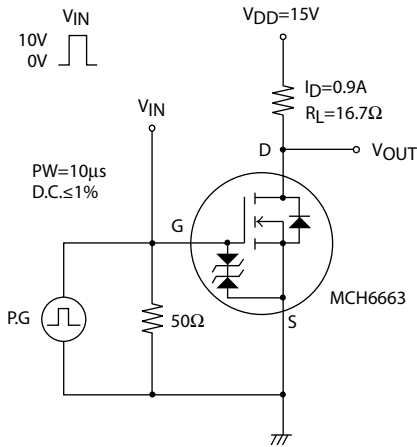
## Electrical Characteristics at Ta = 25°C

| Parameter                                  | Symbol   | Conditions                   | Value |      |      | Unit |
|--------------------------------------------|----------|------------------------------|-------|------|------|------|
|                                            |          |                              | min   | typ  | max  |      |
| [N-channel]                                |          |                              |       |      |      |      |
| Drain to Source Breakdown Voltage          | V(BR)DSS | ID=1mA, VGS=0V               | 30    |      |      | V    |
| Zero-Gate Voltage Drain Current            | IDSS     | VDS=30V, VGS=0V              |       |      | 1    | μA   |
| Gate to Source Leakage Current             | IGSS     | VGS=±16V, VDS=0V             |       |      | ±10  | μA   |
| Gate Threshold Voltage                     | VGS(th)  | VDS=10V, ID=1mA              | 1.2   |      | 2.6  | V    |
| Forward Transconductance                   | gFS      | VDS=10V, ID=0.9A             |       | 1.1  |      | S    |
| Static Drain to Source On-State Resistance | RDS(on)1 | ID=0.9A, VGS=10V             |       | 145  | 188  | mΩ   |
|                                            | RDS(on)2 | ID=0.5A, VGS=4.5V            |       | 245  | 343  | mΩ   |
|                                            | RDS(on)3 | ID=0.5A, VGS=4V              |       | 270  | 378  | mΩ   |
| Input Capacitance                          | Ciss     | VDS=10V, f=1MHz              |       | 88   |      | pF   |
| Output Capacitance                         | Coss     |                              |       | 19   |      | pF   |
| Reverse Transfer Capacitance               | Crss     |                              |       | 11   |      | pF   |
| Turn-ON Delay Time                         | tD(on)   | See specified Test Circuit   |       | 3.4  |      | ns   |
| Rise Time                                  | tR       |                              |       | 3.6  |      | ns   |
| Turn-OFF Delay Time                        | tD(off)  |                              |       | 10.5 |      | ns   |
| Fall Time                                  | tF       |                              |       | 4.0  |      | ns   |
| Total Gate Charge                          | Qg       | VDS=15V, VGS=10V, ID=1.8A    |       | 2.0  |      | nC   |
| Gate to Source Charge                      | Qgs      |                              |       | 0.33 |      | nC   |
| Gate to Drain "Miller" Charge              | Qgd      |                              |       | 0.29 |      | nC   |
| Forward Diode Voltage                      | VSD      | IS=1.8A, VGS=0V              |       | 0.86 | 1.2  | V    |
| [P-channel]                                |          |                              |       |      |      |      |
| Drain to Source Breakdown Voltage          | V(BR)DSS | ID=−1mA, VGS=0V              | −30   |      |      | V    |
| Zero-Gate Voltage Drain Current            | IDSS     | VDS=−30V, VGS=0V             |       |      | −1   | μA   |
| Gate to Source Leakage Current             | IGSS     | VGS=±16V, VDS=0V             |       |      | ±10  | μA   |
| Gate Threshold Voltage                     | VGS(th)  | VDS=−10V, ID=−1mA            | −1.2  |      | −2.6 | V    |
| Forward Transconductance                   | gFS      | VDS=−10V, ID=−0.8A           |       | 1.3  |      | S    |
| Static Drain to Source On-State Resistance | RDS(on)1 | ID=−0.8A, VGS=−10V           |       | 250  | 325  | mΩ   |
|                                            | RDS(on)2 | ID=−0.4A, VGS=−4.5V          |       | 397  | 555  | mΩ   |
|                                            | RDS(on)3 | ID=−0.4A, VGS=−4V            |       | 458  | 641  | mΩ   |
| Input Capacitance                          | Ciss     | VDS=−10V, f=1MHz             |       | 82   |      | pF   |
| Output Capacitance                         | Coss     |                              |       | 22   |      | pF   |
| Reverse Transfer Capacitance               | Crss     |                              |       | 16   |      | pF   |
| Turn-ON Delay Time                         | tD(on)   | See specified Test Circuit   |       | 4.0  |      | ns   |
| Rise Time                                  | tR       |                              |       | 3.3  |      | ns   |
| Turn-OFF Delay Time                        | tD(off)  |                              |       | 12   |      | ns   |
| Fall Time                                  | tF       |                              |       | 5.4  |      | ns   |
| Total Gate Charge                          | Qg       | VDS=−15V, VGS=−10V, ID=−1.5A |       | 2.2  |      | nC   |
| Gate to Source Charge                      | Qgs      |                              |       | 0.36 |      | nC   |
| Gate to Drain "Miller" Charge              | Qgd      |                              |       | 0.49 |      | nC   |
| Forward Diode Voltage                      | VSD      | IS=−1.5A, VGS=0V             |       | −0.9 | −1.5 | V    |

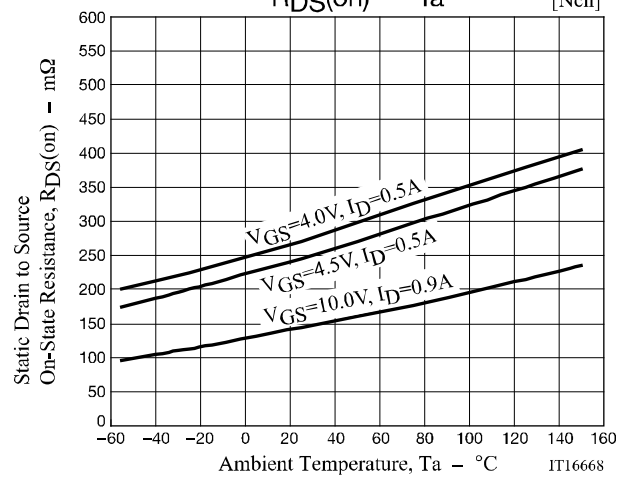
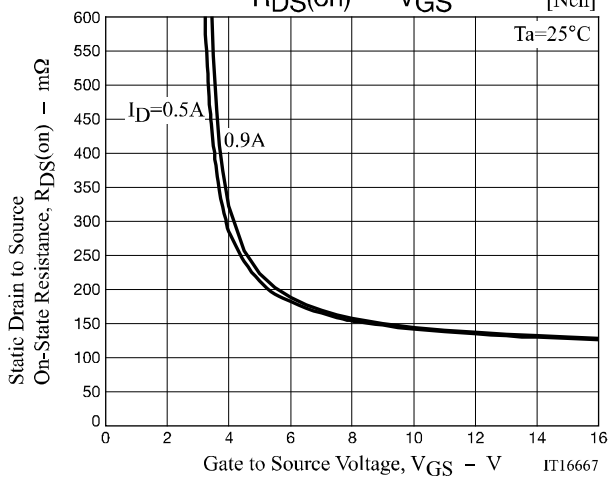
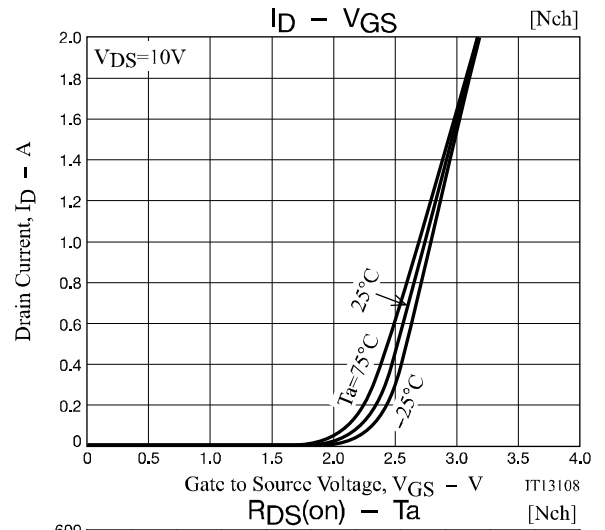
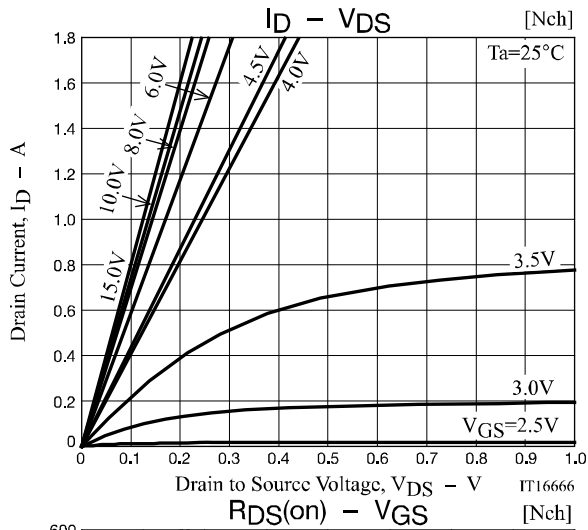
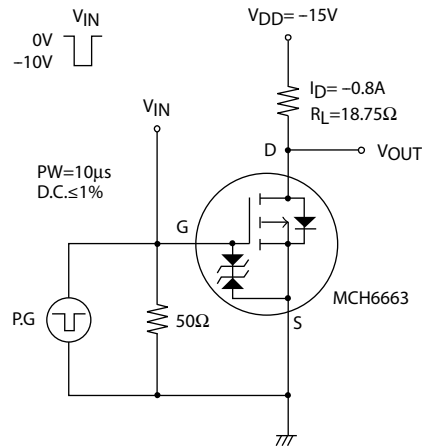
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

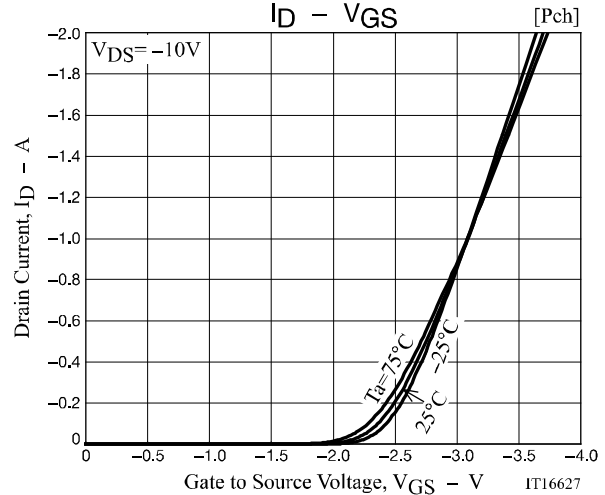
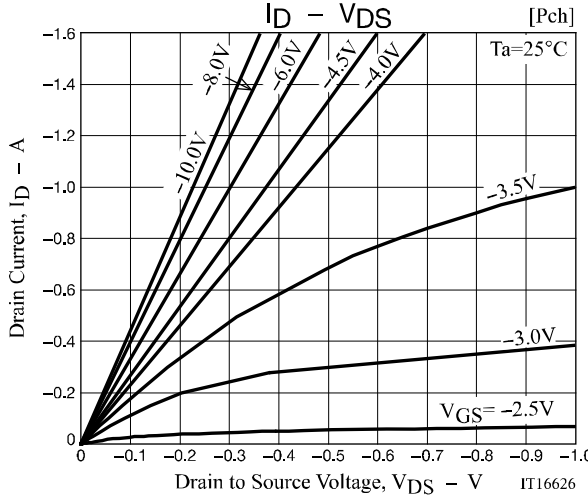
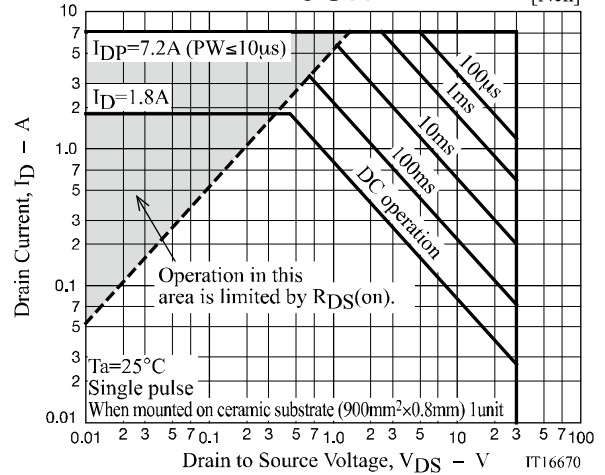
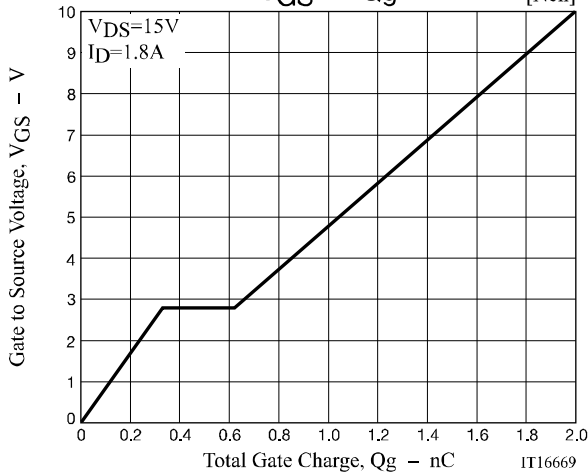
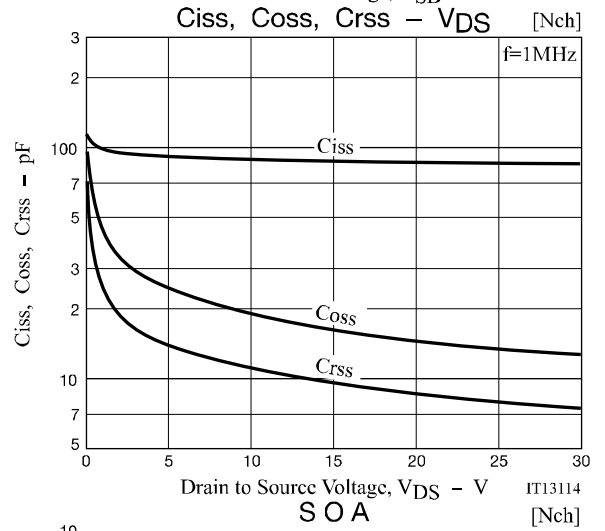
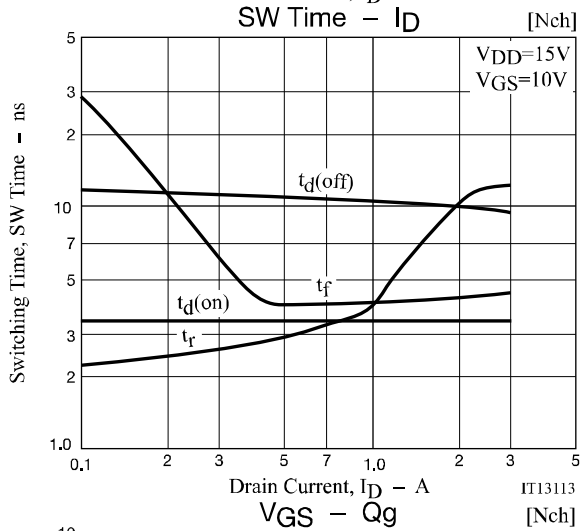
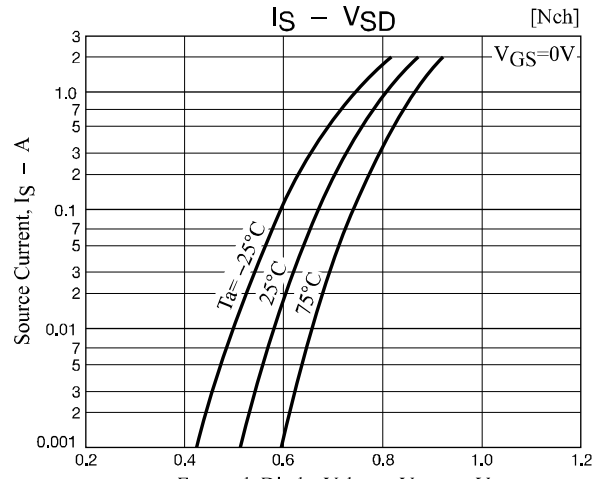
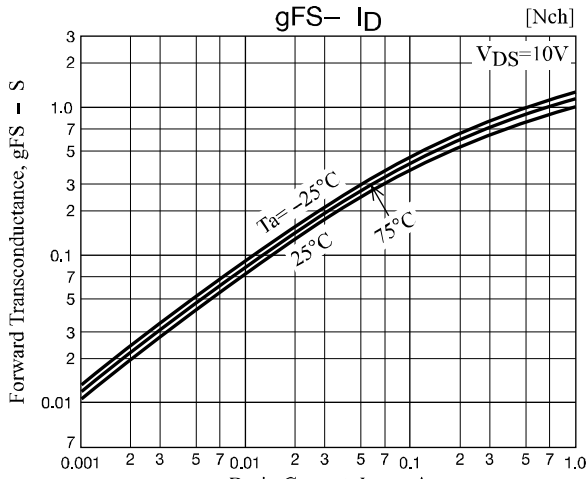
# Switching Time Test Circuit

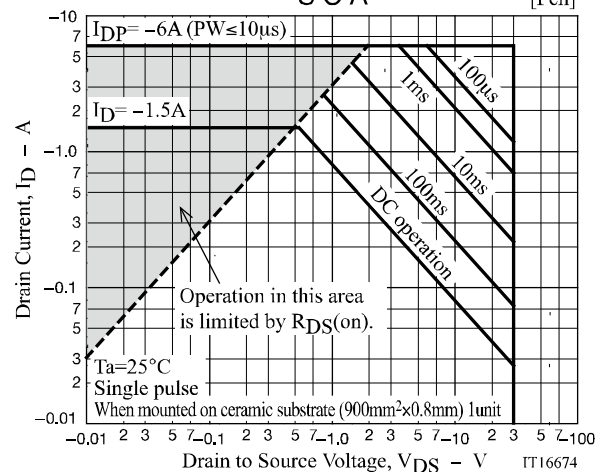
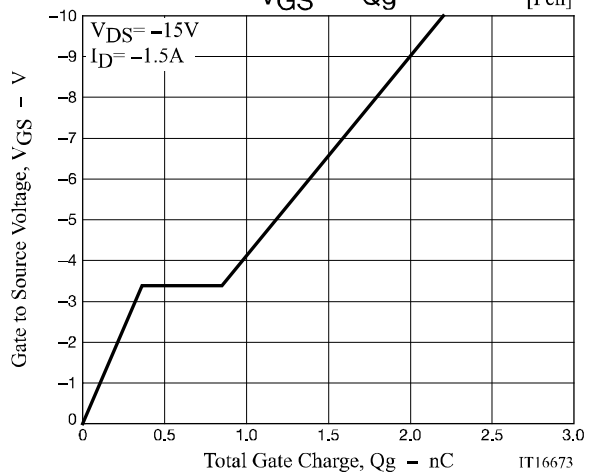
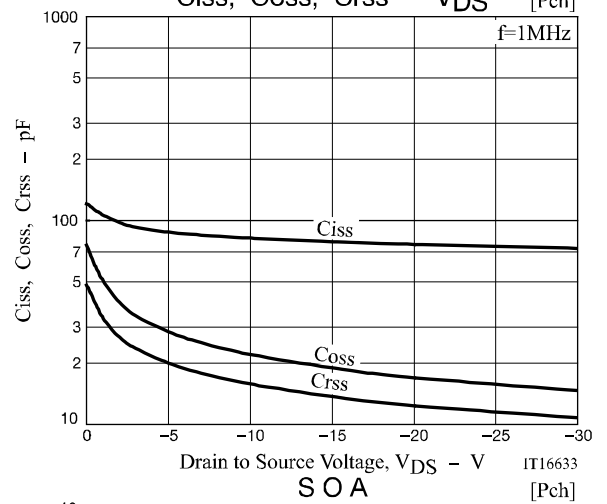
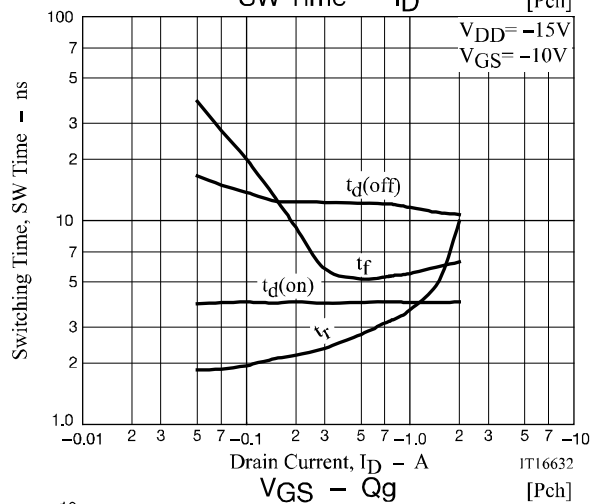
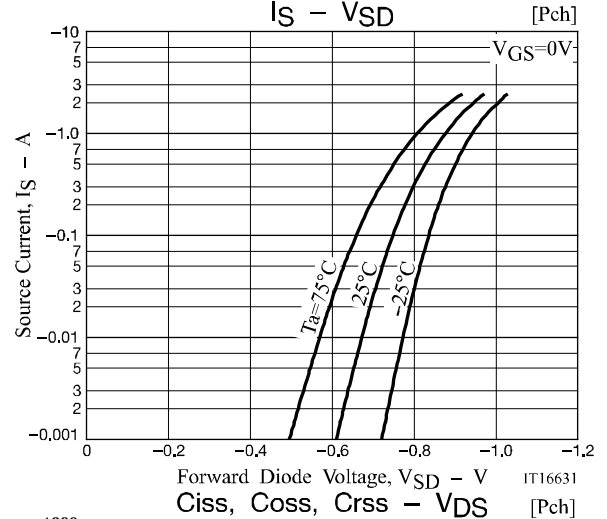
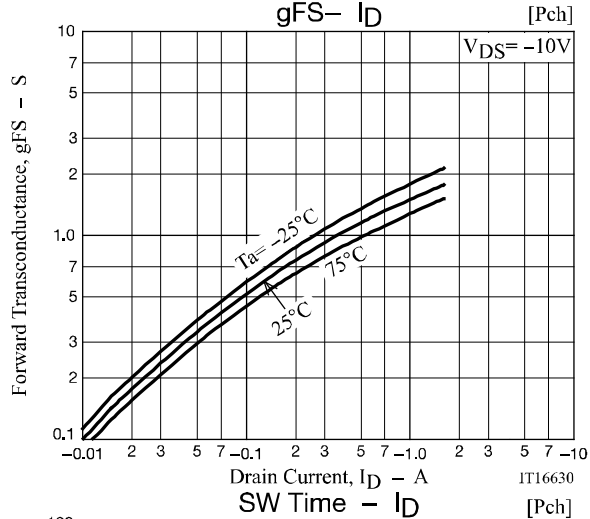
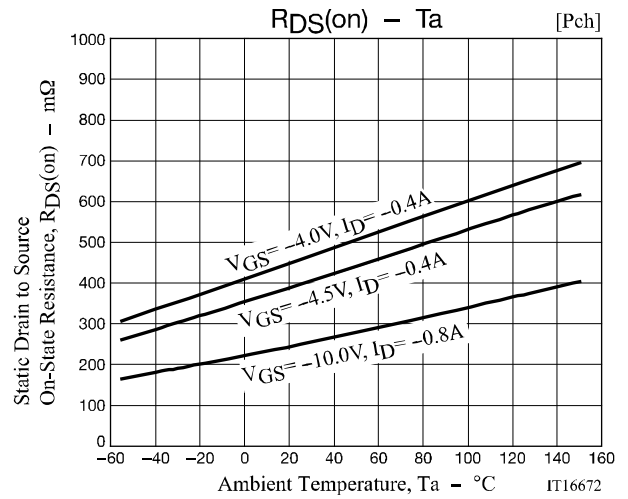
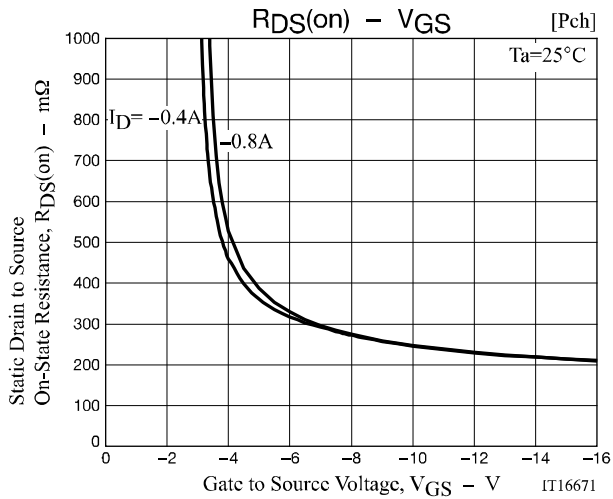
[N-channel]

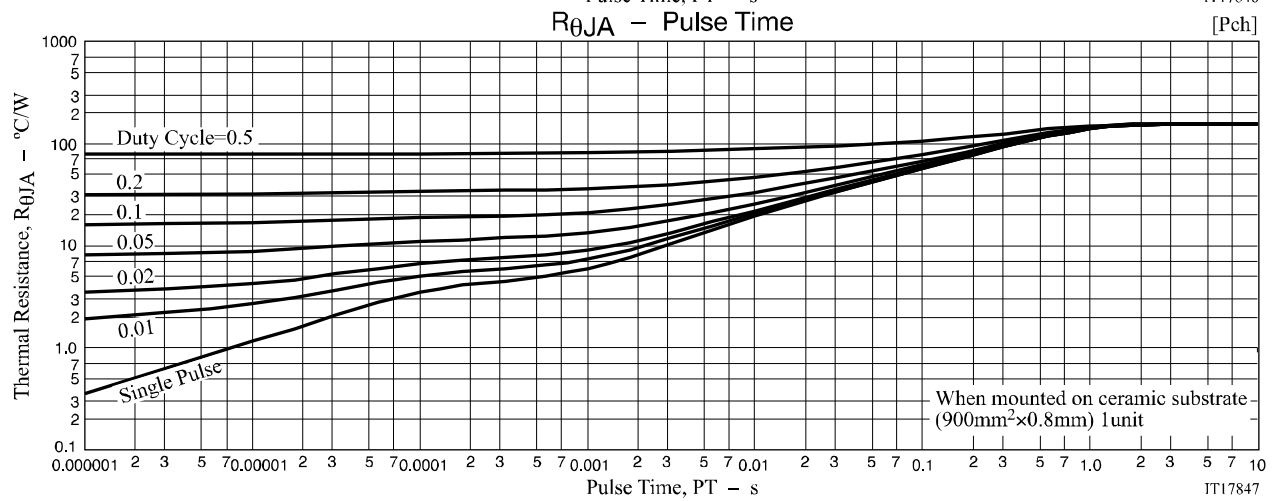
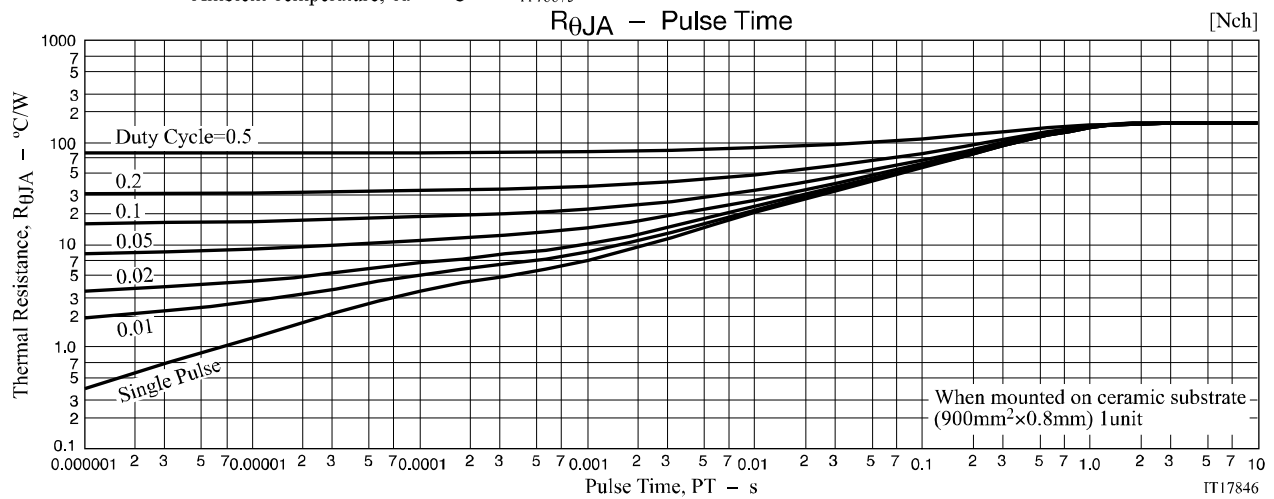
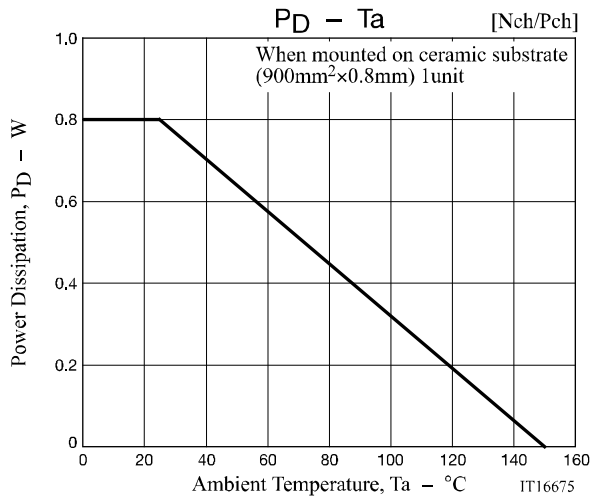


[P-channel]









## Package Dimensions

MCH6663-TL-H / MCH6663-TL-W

### MCPH6

CASE 419AS

ISSUE O

unit : mm

1 : Source1

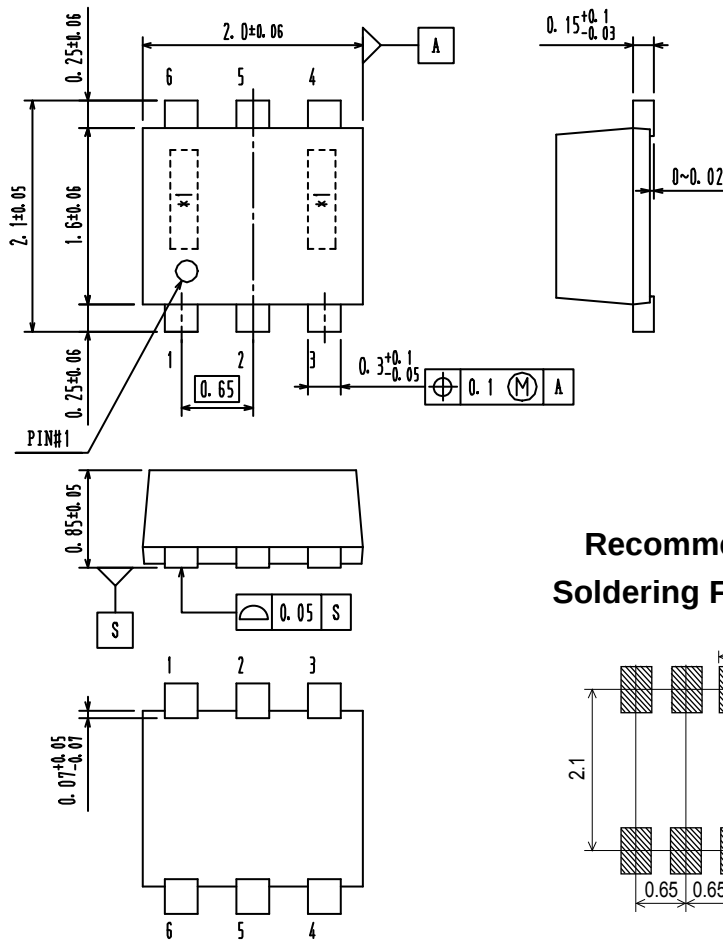
2 : Gate1

3 : Drain2

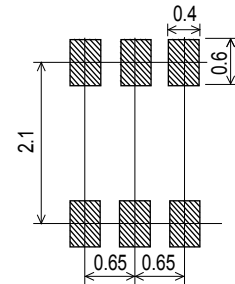
4 : Source2

5 : Gate 2

6 : Drain1



### Recommended Soldering Footprint



## ORDERING INFORMATION

| Device       | Package                          | Shipping                 | Note                        |
|--------------|----------------------------------|--------------------------|-----------------------------|
| MCH6663-TL-H | MCPH6<br>SC-88, SC-70-6, SOT-363 | 3,000 pcs. / Tape & Reel | Pb-Free<br>and Halogen Free |
| MCH6663-TL-W |                                  |                          |                             |

Note on usage : Since the MCH6663 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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